

2SC5912

Silicon NPN triple diffusion mesa type

Horizontal deflection output for TV

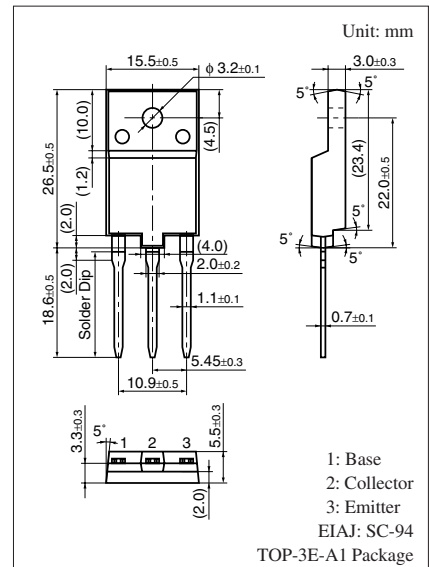
■ Features

- High breakdown voltage: $V_{CBO} \geq 1500$ V
- Wide safe operation area
- Built-in dumper diode

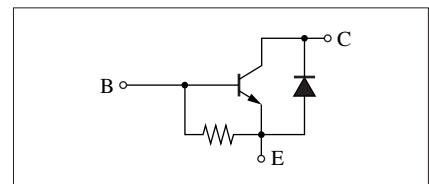
■ Absolute Maximum Ratings $T_C = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	1500	V
Collector-emitter voltage (E-B short)	V_{CES}	1500	V
Emitter-base voltage (Collector open)	V_{EBO}	7	V
Base current	I_B	3	A
Collector current	I_C	10	A
Peak collector current *	I_{CP}	15	A
Collector power dissipation	P_C	40	W
	$T_a = 25^\circ\text{C}$	3	
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Note) *: Non-repetitive peak collector current



Internal Connection



■ Electrical Characteristics $T_C = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = 500$ mA, $I_C = 0$	7			V
Forward voltage	V_F	$I_F = 5$ A			-2	V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 1000$ V, $I_E = 0$			50	μA
		$V_{CB} = 1500$ V, $I_E = 0$			1	mA
Forward current transfer ratio	h_{FE}	$V_{CE} = 5$ V, $I_C = 5$ A	5		10	—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 5$ A, $I_B = 1.25$ A			2.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 5$ A, $I_B = 1.25$ A			1.5	V
Transition frequency	f_T	$V_{CE} = 10$ V, $I_C = 0.1$ A, $f = 0.5$ MHz		3		MHz
Storage time	t_{stg}	$I_C = 5$ A, Resistance loaded			5.0	μs
Fall time	t_f	$I_{B1} = 1.25$ A, $I_{B2} = -2.5$ A			0.5	μs

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

